

ON Semiconductor

Is Now

onsemi™

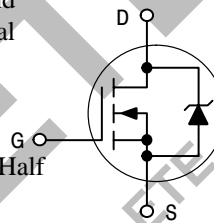
To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

Designer's™ Data Sheet
TMOS E-FET™
Power Field Effect Transistor
N-Channel Enhancement-Mode Silicon
Gate

This advanced TMOS E-FET is designed to withstand high energy in the avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for low voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional safety margin against unexpected voltage transients.

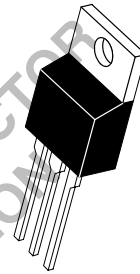
- Designed to Eliminate the Need for External Zener Transient Suppressor — Absorbs High Energy in the Avalanche Mode
- Commutating Safe Operating Area (CSOA) Specified for Use in Half and Full Bridge Circuits
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature



MTP12N10E

Motorola Preferred Device

TMOS POWER FET
12 AMPERES
100 VOLTS
 $R_{DS(on)} = 0.16 \text{ OHM}$



CASE 221A-06, Style 5
TO-220AB

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	100	Vdc
Gate-Source Voltage — Continuous — Single Pulse ($t_p \leq 50 \mu\text{s}$)	V_{GS}	± 20 ± 40	Vdc
Drain Current — Continuous — Single Pulse ($t_p \leq 10 \mu\text{s}$)	I_D I_{DM}	12 30	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	79 0.53	Watts W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

UNCLAMPED DRAIN-TO-SOURCE AVALANCHE CHARACTERISTICS ($T_J \leq 175^\circ\text{C}$)

Single Pulse Drain-to-Source Avalanche Energy — Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 25 \text{ V}$, $V_{GS} = 10 \text{ V}$, $L = 4.03 \text{ mH}$, $R_G = 25 \Omega$, Peak $I_L = 12 \text{ A}$) (See Figures 15, 16 and 17)	E_{AS}	290	mJ
---	----------	-----	----

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1.9 62.5	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

E-FET and Designer's are trademarks of Motorola, Inc. TMOS is a registered trademark of Motorola, Inc.

Preferred devices are Motorola recommended choices for future use and best overall value.

MTP12N10E

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V _{GS} = 0, I _D = 250 μAdc) Temperature Coefficient (positive)	V _{(BR)DSS}	100 —	— 110	— —	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{DS} = 100 V, V _{GS} = 0) (V _{DS} = 100 V, V _{GS} = 0, T _J = 150°C)	I _{DSS}	— —	— —	10 100	μA
Gate-Body Leakage Current, Forward (V _{GSF} = 20 Vdc, V _{DS} = 0)	I _{GSSF}	—	—	100	nAdc
Gate-Body Leakage Current, Reverse (V _{GSR} = 20 Vdc, V _{DS} = 0)	I _{GSSR}	—	—	100	nAdc

ON CHARACTERISTICS*

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 250 μAdc) Temperature Coefficient (negative)	V _{GS(th)}	2.0 —	3.0 6.0	4.0 —	Vdc mV/°C
Static Drain-Source On-Resistance (V _{GS} = 10 Vdc, I _D = 6.0 Adc)	R _{DS(on)}	—	0.125	0.16	Ohm
Drain-Source On-Voltage (V _{GS} = 10 Vdc) (I _D = 12 Adc) (I _D = 6.0 Adc, T _J = 150°C)	V _{DS(on)}	— —	1.5 1.4	2.4 1.92	Vdc
Forward Transconductance (V _{DS} ≥ 15 V, I _D = 6.0 A)	g _{FS}	4.0	5.0	—	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz) See Figure 14	C _{iss}	—	600	—	pF
Reverse Transfer Capacitance		C _{rss}	—	70	—	
Output Capacitance		C _{oss}	—	230	—	

SWITCHING CHARACTERISTICS (T_J = 100°C)

Turn-On Delay Time	(V _{DD} = 50 V, I _D = 12 A, V _{GS} = 10 V, R _G = 12 Ω) See Figure 7	t _{d(on)}	—	10	—	ns
Rise Time		t _r	—	64	—	
Turn-Off Delay Time		t _{d(off)}	—	21	—	
Fall Time		t _f	—	30	—	
Gate Charge	(V _{DS} = 80 V, I _D = 12 A, V _{GS} = 10 Vdc) See Figures 5 and 6	Q _T	—	18	26	nC
		Q ₁	—	4.0	—	
		Q ₂	—	10	—	
		Q ₃	—	8.0	—	

SOURCE-DRAIN DIODE CHARACTERISTICS*

Forward On-Voltage	(I _S = 12 A, V _{GS} = 0) (I _S = 12 A, V _{GS} = 0, T _J = 150°C)	V _{SD}	— —	1.0 0.83	2.5 —	Vdc
Reverse Recovery Time	(I _S = 12 A, V _{GS} = 0, di _S /dt = 100 A/μs, V _R = 50 V)	t _{rr}	—	110	—	ns

INTERNAL PACKAGE INDUCTANCE

Internal Drain Inductance (Measured from the contact screw on tab to center of die) (Measured from the drain lead 0.25" from package to center of die)	L _d	— —	3.5 4.5	— —	nH
Internal Source Inductance (Measured from the source lead 0.25" from package to source bond pad)	L _s	—	7.5	—	

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

MTP12N10E

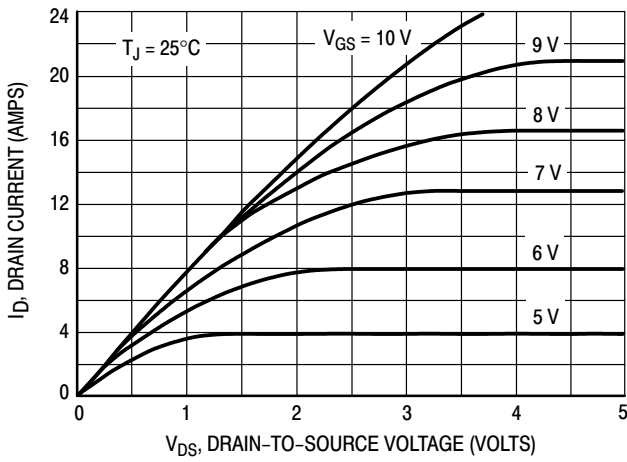


Figure 1. On-Region Characteristics

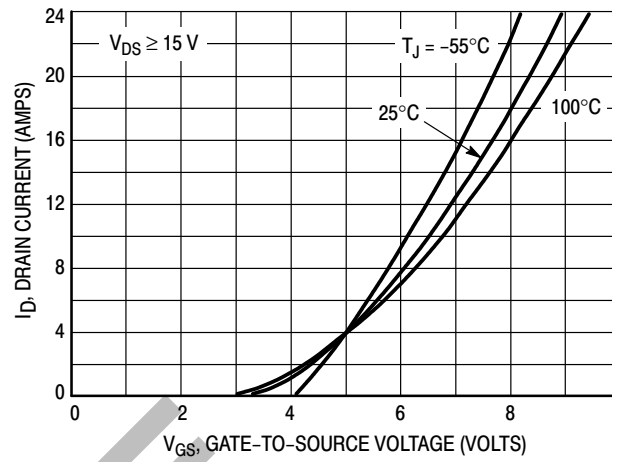


Figure 2. Transfer Characteristics

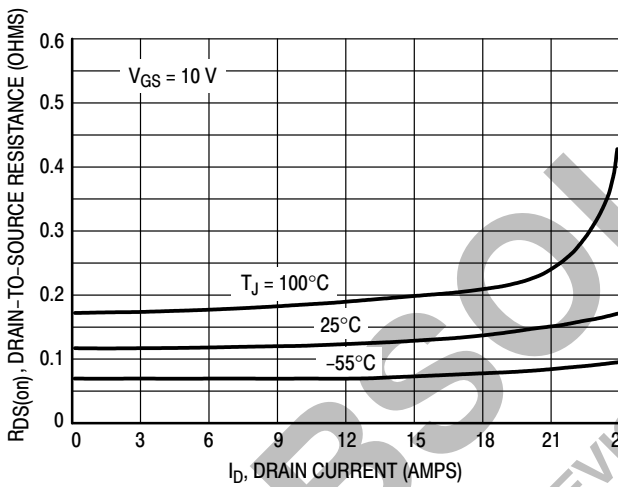


Figure 3. On-Resistance versus Drain Current

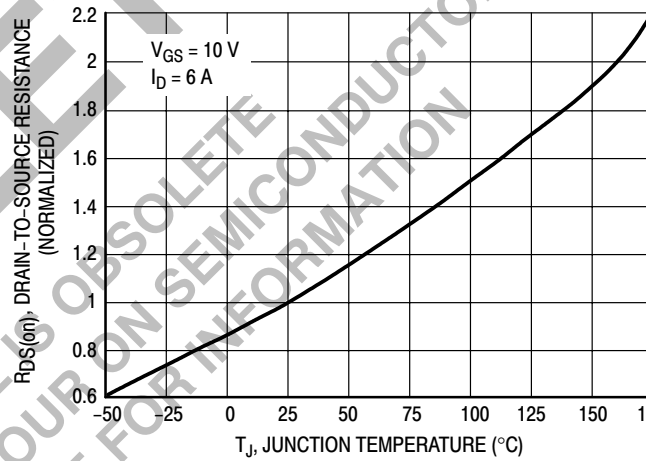


Figure 4. On-Resistance Variation with Temperature

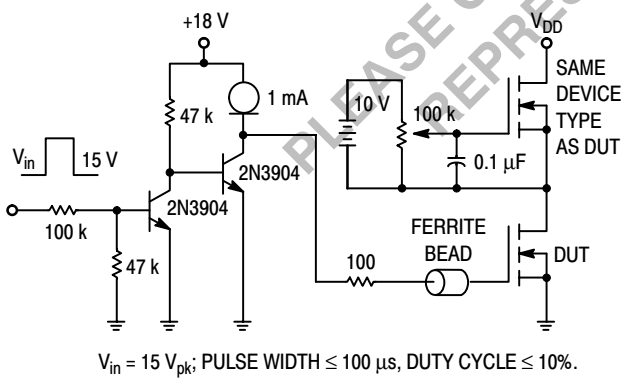


Figure 5. Gate Charge Test Circuit

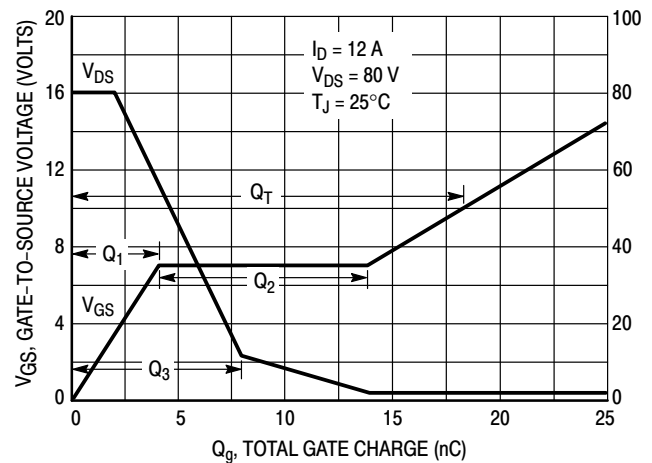


Figure 6. Gate-to-Source and Drain-to-Source Voltage versus Gate Charge

SAFE OPERATING AREA INFORMATION

FORWARD BIASED SAFE OPERATING AREA

The FBSOA curves define the maximum drain-to-source voltage and drain current that a device can safely handle when it is forward biased, or when it is on, or being turned on. Because these curves include the limitations of simultaneous high voltage and high current, up to the rating of the device, they are especially useful to designers of linear systems. The curves are based on a case temperature of 25°C and a maximum junction temperature of 175°C. Limitations for repetitive pulses at various case temperatures can be determined by using the thermal response curves. Motorola Application Note, AN569, "Transient Thermal Resistance—General Data and Its Use" provides detailed instructions.

SWITCHING SAFE OPERATING AREA

The switching safe operating area (SOA) of Figure 9 is the boundary that the load line may traverse without incurring damage to the MOSFET. The fundamental limits are the peak current, I_{DM} and the breakdown voltage, BV_{DSS} . The switching SOA shown in Figure 9 is applicable for both turn-on and turn-off of the devices for switching times less than one microsecond.

The power averaged over a complete switching cycle must be less than:

$$\frac{T_{J(max)} - T_C}{R_{\theta JC}}$$

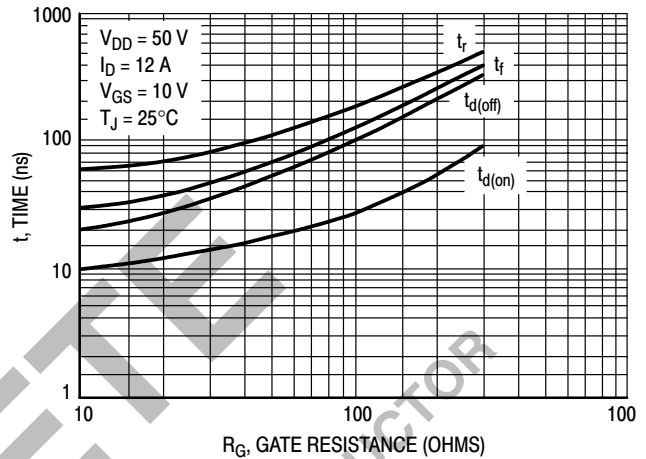


Figure 7. Resistive Switching Time versus Gate Resistance

OBSOLETE

THIS DEVICE IS OBSOLETE. PLEASE CONTACT YOUR ON SEMICONDUCTOR REPRESENTATIVE FOR INFORMATION.

MTP12N10E

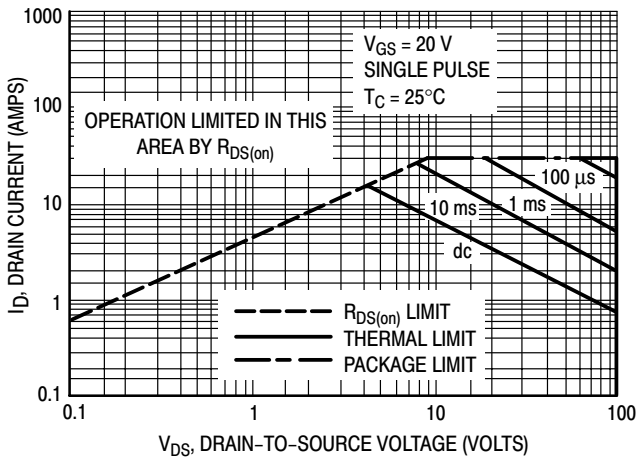


Figure 8. Maximum Rated Forward Biased Safe Operating Area

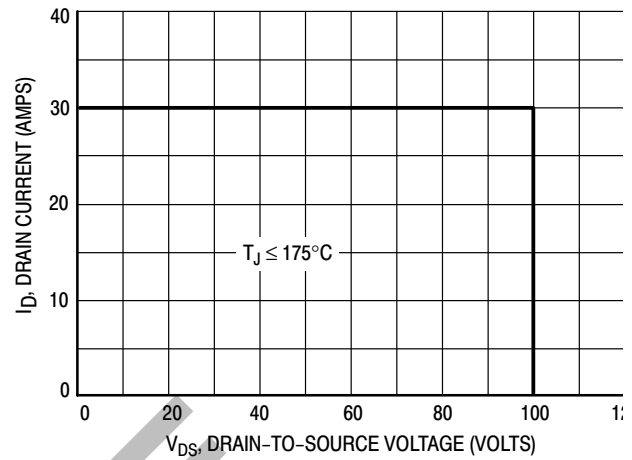


Figure 9. Maximum Rated Switching Safe Operating Area

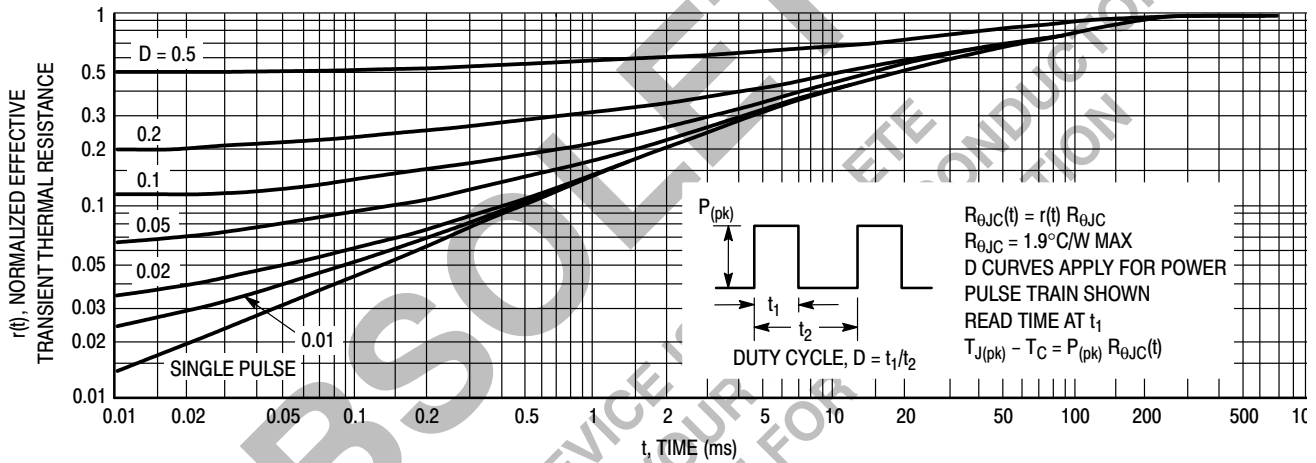


Figure 10. Thermal Response

COMMUTATING SAFE OPERATING AREA (CSOA)

The Commutating Safe Operating Area (CSOA) of Figure 12 defines the limits of safe operation for commutated source-drain current versus re-applied drain voltage when the source-drain diode has undergone forward bias. The curve shows the limitations of I_{FM} and peak V_{DS} for a given rate of change of source current. It is applicable when waveforms similar to those of Figure 11 are present. Full or half-bridge PWM DC motor controllers are common applications requiring CSOA data.

Device stresses increase with increasing rate of change of source current so di_s/dt is specified with a maximum value. Higher values of di_s/dt require an appropriate derating of I_{FM} , peak V_{DS} or both. Ultimately di_s/dt is limited

primarily by device, package, and circuit impedances. Maximum device stress occurs during t_{rr} as the diode goes from conduction to reverse blocking.

$V_{DS(pk)}$ is the peak drain-to-source voltage that the device must sustain during commutation; I_{FM} is the maximum forward source-drain diode current just prior to the onset of commutation.

V_R is specified at rated BV_{DSS} to ensure that the CSOA stress is maximized as I_S decays from I_{RM} to zero.

R_{GS} should be minimized during commutation. T_J has only a second order effect on CSOA.

Stray inductances in Motorola's test circuit are assumed to be practical minimums.

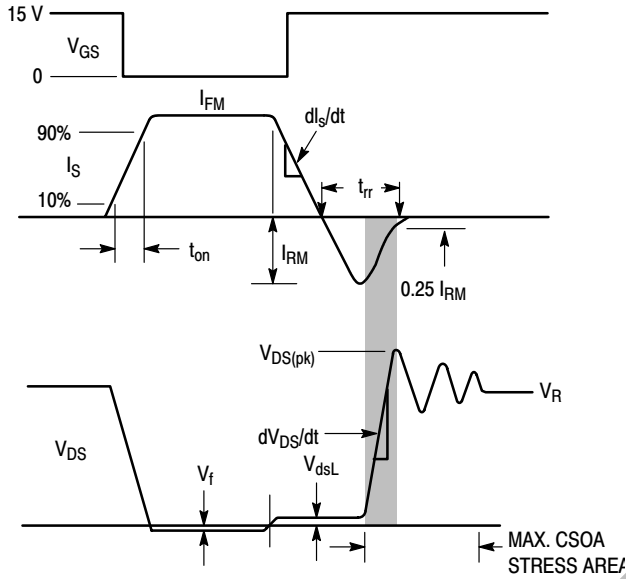


Figure 11. Commutating Waveforms

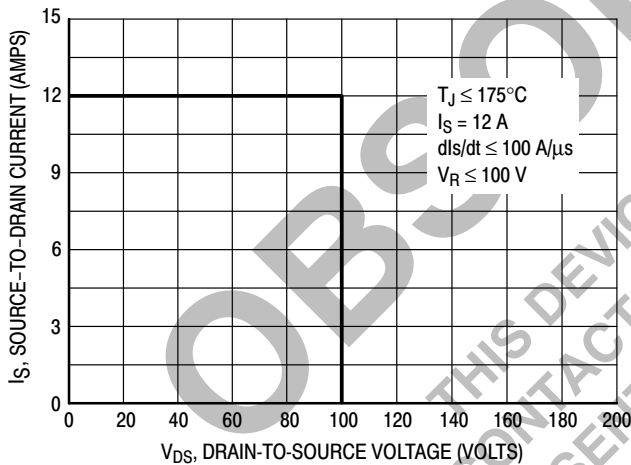


Figure 12. Commutating Safe Operating Area (CSOA)

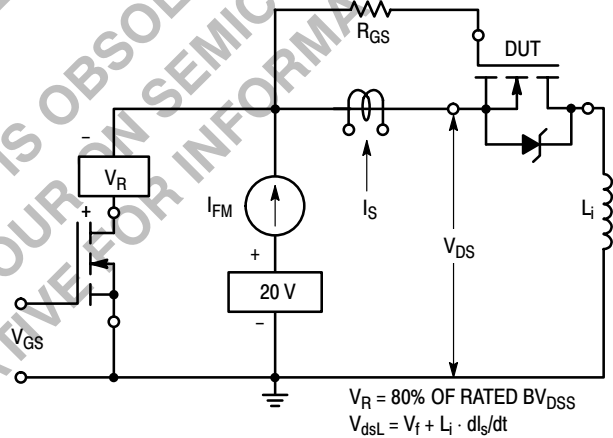



Figure 13. Commutating Safe Operating Area Test Circuit

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and  are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

MTP12N10E

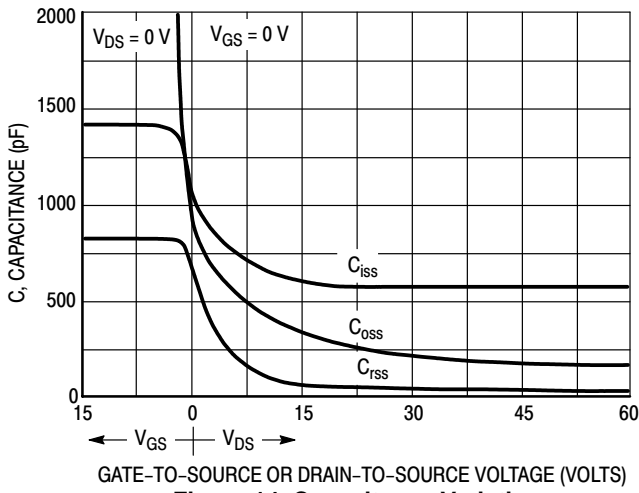


Figure 14. Capacitance Variation

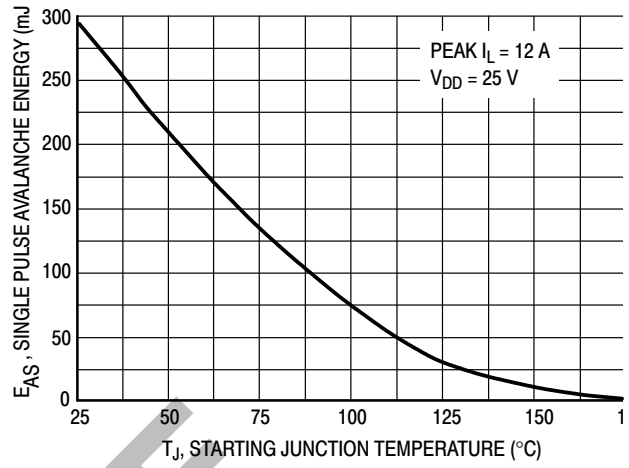


Figure 15. Maximum Avalanche Energy versus Starting Junction Temperature

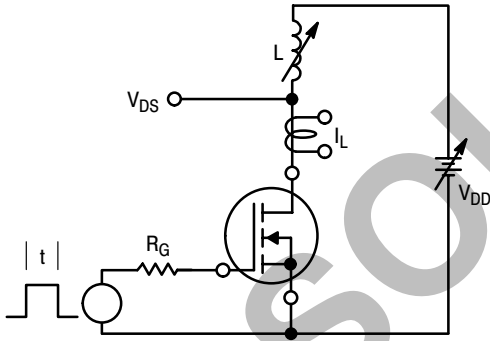


Figure 16. Unclamped Inductive Switching Test Circuit

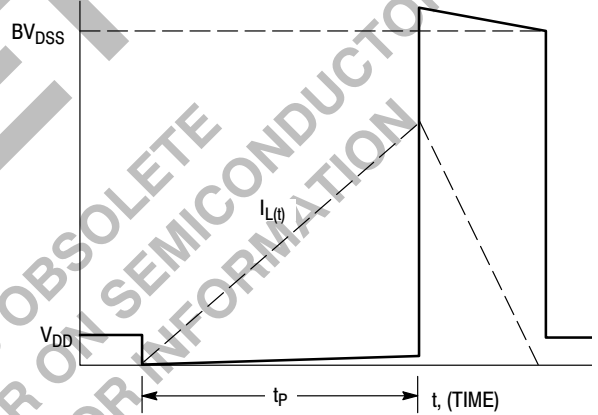
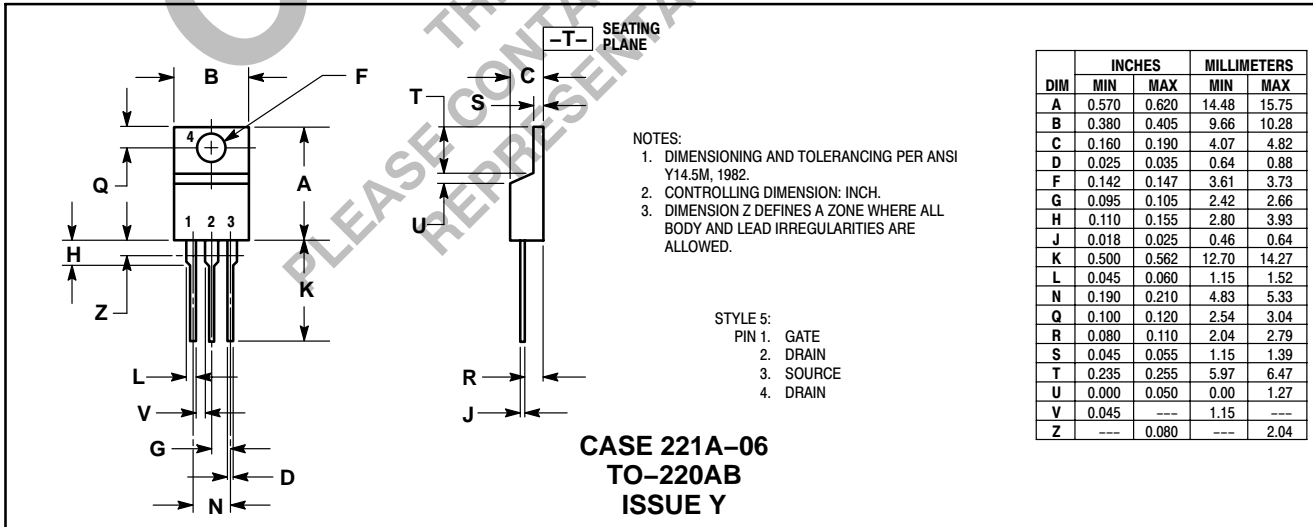


Figure 17. Unclamped Inductive Switching Waveforms

PACKAGE DIMENSIONS



OBSOLETE
THIS DEVICE IS OBSOLETE
PLEASE CONTACT YOUR ON SEMICONDUCTOR
REPRESENTATIVE FOR INFORMATION

How to reach us:

USA / EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609
INTERNET: <http://Design-NET.com>

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

